

General Features

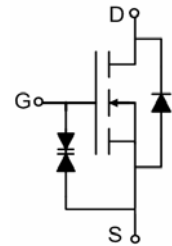
- $V_{DS} = 100\text{ V}$, $I_D = 0.17\text{ A}$
 $R_{DS(ON)} < 7.2\Omega @ V_{GS}=10\text{ V}$
 $R_{DS(ON)} < 8\Omega @ V_{GS}=4.5\text{ V}$
- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- ESD 2KV HBM

Application

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays



SOT-23-3



Schematic Diagram

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
V SMBSS123K-S2	V SMBSS123K	SOT-23-3	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_A = 25^\circ\text{C}$	I_D	0.17	A
	$T_A = 100^\circ\text{C}$		0.12	
Drain Current-Pulsed (Note 1)		I_{DM}	0.68	A
Maximum Power Dissipation		P_D	0.35	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{ V}$ $I_D=250\mu\text{ A}$	100	-	-	V

Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 1	μA
		$V_{GS}=\pm 20V, V_{DS}=0V$	-		± 10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.3	1.9	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=0.17A$	-	6.5	7.2	Ω
		$V_{GS}=4.5V, I_D=0.17A$	-	7	8	Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=0.17A$	0.1	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$	-	29	50	PF
Output Capacitance	C_{oss}		-	10	25	PF
Reverse Transfer Capacitance	C_{rss}		-	2	5	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=0.17A$ $V_{GS}=10V, R_{GEN}=10\Omega$	-	8	-	nS
Turn-on Rise Time	t_r		-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	13	-	nS
Turn-Off Fall Time	t_f		-	16	-	nS
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=0.17A,$ $V_{GS}=10V$	-	1.7	3	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=0.17A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	0.17	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics



Figure 1: Switching Test Circuit

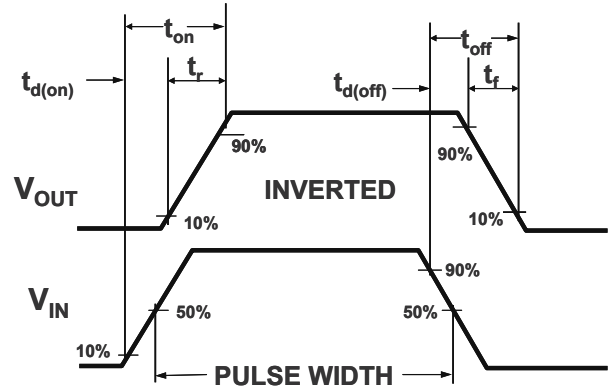


Figure 2: Switching Waveforms

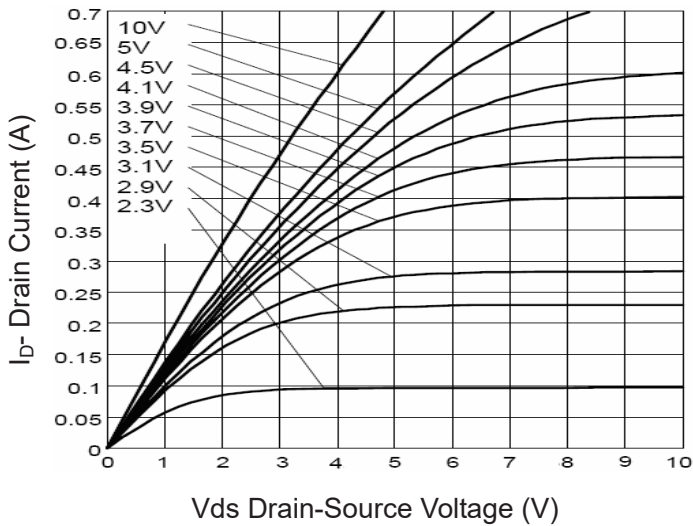


Figure 3 Output Characteristics

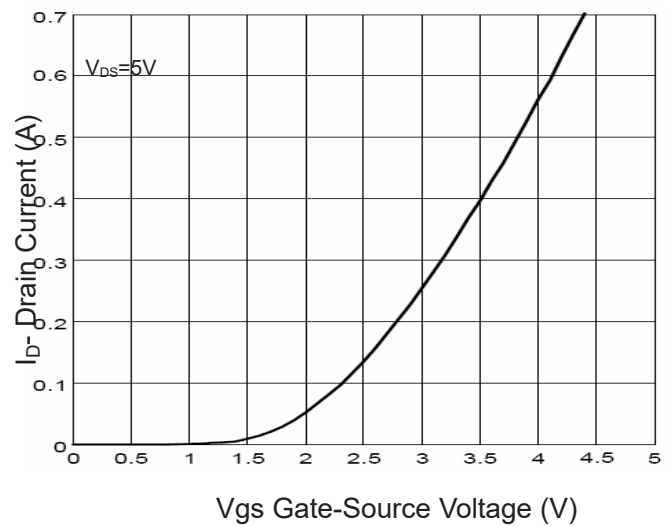


Figure 4 Transfer Characteristics

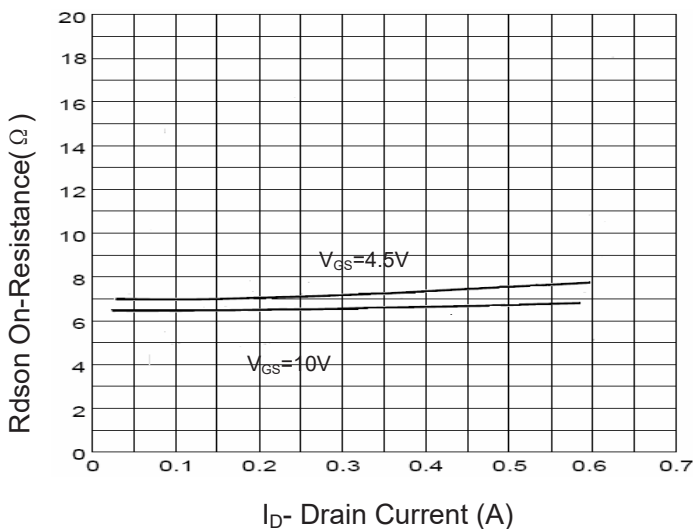


Figure 5 Drain-Source On-Resistance

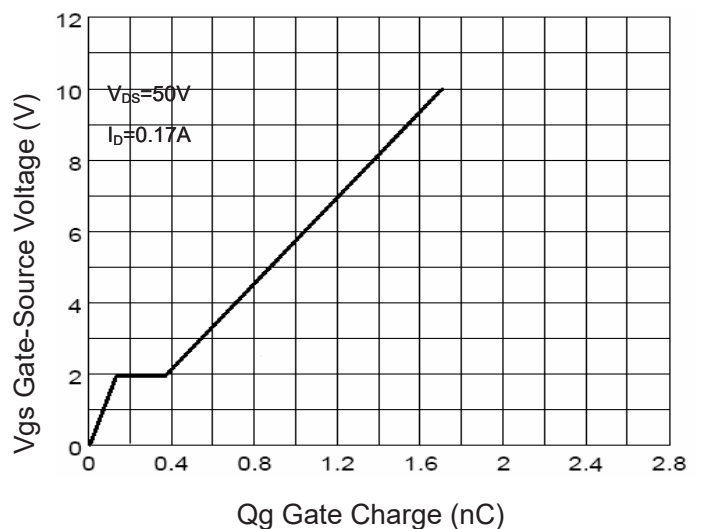


Figure 6 Gate Charge

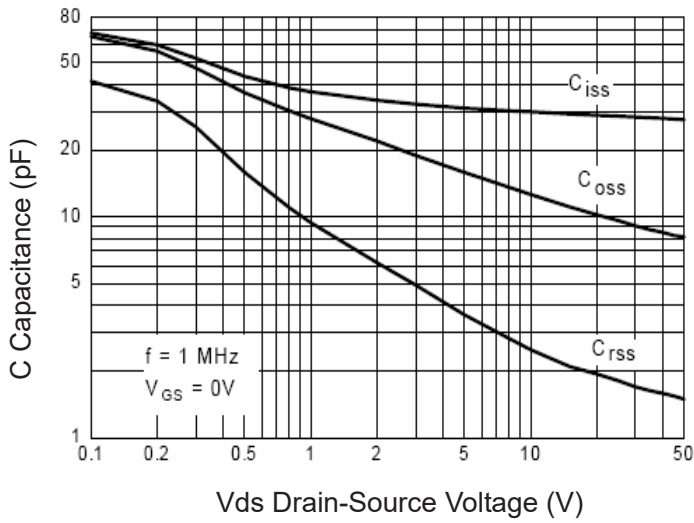


Figure 7 Capacitance vs V_{ds}

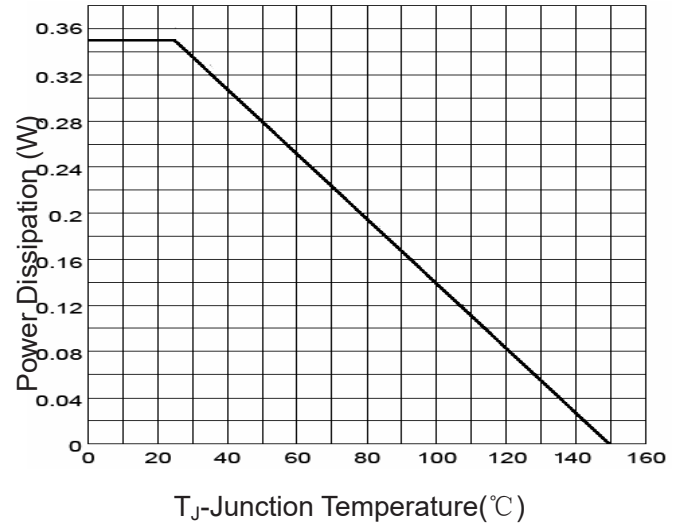


Figure 9 Power De-rating

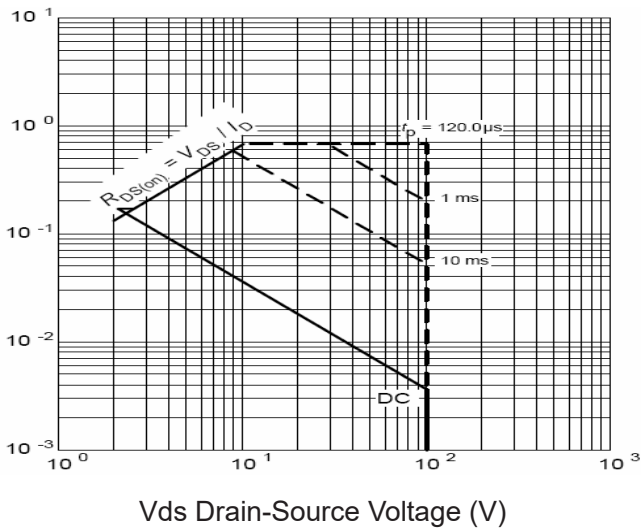


Figure 8 Safe Operation Area

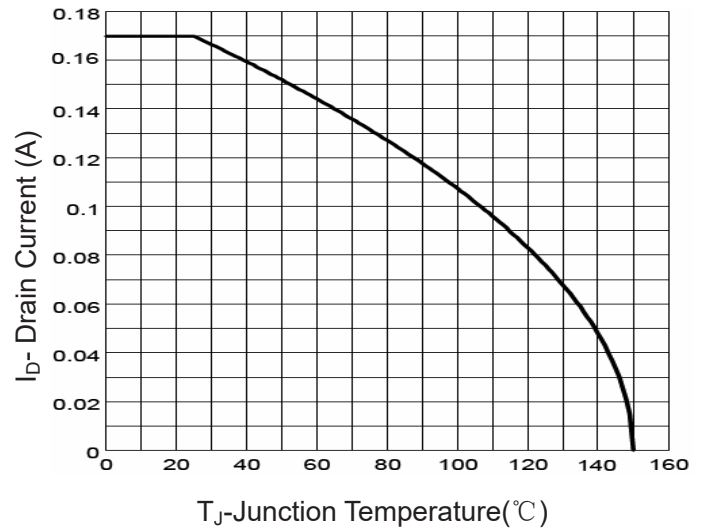


Figure 10 Current De-rating

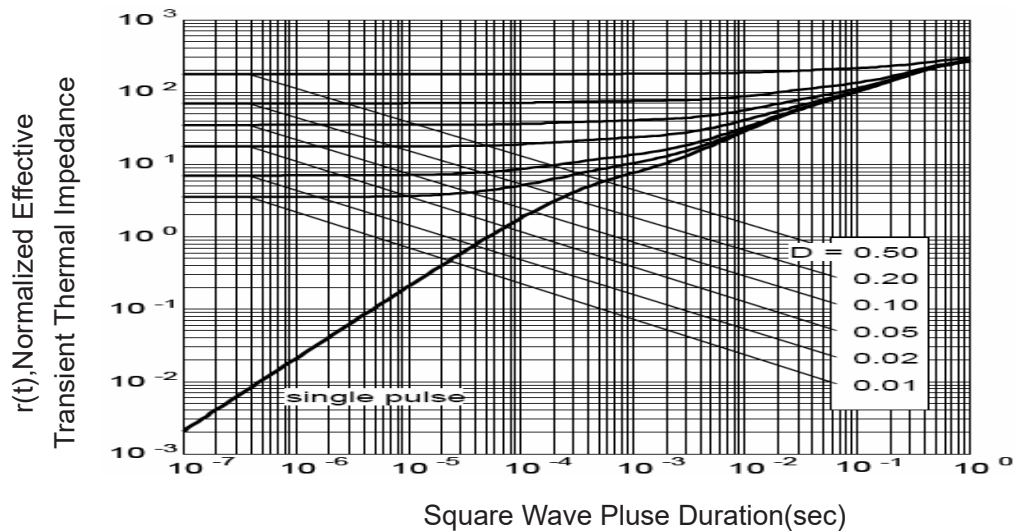


Figure 11 Normalized Maximum Transient Thermal Impedance